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Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, I²C, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	74
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 38x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkv42f256vll16

1 Ratings

1.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human-body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105 °C	-100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-up Test*.

1.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	Digital pin input voltage (except open drain pins)	–0.3	VDD + 0.3[1]	V
	Open drain pins (PTC6 and PTC7)	–0.3	5.5	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. Maximum value of V_{IO} (except open drain pins) must be 3.8 V.

1.5 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 1 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

Table 1. Absolute Maximum Ratings (V_{SS} = 0 V, V_{SSA} = 0 V)

Symbol	Description	Notes[1]	Min	Max	Unit
V_{DD}	Supply Voltage Range		-0.3	4.0	V
V_{DDA}	Analog Supply Voltage Range		-0.3	4.0	V
V_{REFHx}	ADC High Voltage Reference		-0.3	4.0	V
V_{REFLx}	ADC Low Voltage Reference		-0.3	0.3	V
ΔV_{DD}	Voltage difference V_{DD} to V_{DDA}		-0.3	0.3	V
ΔV_{SS}	Voltage difference V_{SS} to V_{SSA}		-0.3	0.3	V
V_{IN}	Digital Input Voltage Range	Pin Groups 1, 2	-0.3	4.0	V
V_{OSC}	Oscillator Input Voltage Range	Pin Group 4	-0.4	4.0	V
V_{INA}	Analog Input Voltage Range	Pin Group 3	-0.3	4.0	V
I_{IC}	Input clamp current, per pin (V_{IN} < 0)		—	-20.0	mA
I_{OC}	Output clamp current, per pin (V_O < 0)[2]		—	-20.0	mA
V_{OUT}	Output Voltage Range (Normal Push-Pull mode)	Pin Group 1	-0.3	4.0	V
V_{OUTOD}	Output Voltage Range (Open Drain mode)	Pin Group 2	-0.3	5.5	V
V_{OUT_DAC}	DAC Output Voltage Range	Pin Group 5	-0.3	4.0	V
T_A	Ambient Temperature Industrial		-40	105	°C
T_{STG}	Storage Temperature Range (Extended Industrial)		-55	150	°C

1. Default Mode
   - Pin Group 1: GPIO, TDI, TDO, TMS, TCK
   - Pin Group 2: $\overline{\text{RESET}}$, PORTC6, and PORTC7
   - Pin Group 3: ADC and Comparator Analog Inputs

2. If the ADC is enabled, minimum V_{DD} is 2.7 V and minimum V_{DDA} is 2.7 V. ADCA and ADCB are not guaranteed to operate below 2.7 V. All other analog modules besides the ADC and Nano-edge will operate down to 1.71 V.
3. If the Nano-edge is enabled, minimum V_{DD} is 3.0 V and minimum V_{DDA} is 3.0 V. Nano-edge is not guaranteed to operate below 3.0 V. All other analog modules besides the ADC and Nano-edge will operate down to 1.71 V.

2.2.2 LVD and POR operating requirements

Table 3. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{OH}	Output high voltage — normal drive pad					
		V_{DD} – 0.5	—	—	V	
		V_{DD} – 0.5	—	—	V	

Table continues on the next page...

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -10mA • 1.71 V ≤V_{DD} ≤ 2.7 V, I_{OH} = -5mA					
	Output high voltage — High drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -20mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -10mA	 V_{DD} – 0.5 V_{DD} – 0.5	 — —	 — —	 V V	1
I_{OHT}	Output high current total for all ports	—	—	100	mA	
V_{OL}	Output low voltage — open drain pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = 3 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = 1 mA	— —	— —	0.5 0.5	V V	2
V_{OL}	Output low voltage — normal drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 10 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 5 mA	— —	— —	0.5 0.5	V V	
	Output low voltage — high drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 20 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 10 mA	— —	— —	0.5 0.5	V V	1
I_{OLT}	Output low current total for all ports	—	—	100	mA	
I_{IN}	Input leakage current, analog and digital pins • V_{SS} ≤ V_{IN} ≤ V_{DD}	—	0.002	0.5	µA	3
R_{PU}	Internal pullup resistors(except RTC_WAKEUP pins)	20	—	50	kΩ	4
R_{PD}	Internal pulldown resistors	20	—	50	kΩ	5

1. High drive pads are PTB0, PTB1, PTC3, PTC4, PTD4, PTD5, PTD6 and PTD7.
2. Open drain pads are PTC6 and PTC7.
3. Measured at VDD=3.6V
4. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
5. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 100 MHz
- Bus and flash clock = 25 MHz
- FEI clock mode

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	µs	
	• VLLS0 → RUN	—	—	173	µs	
	• VLLS1 → RUN	—	—	172	µs	
	• VLLS2 → RUN	—	—	96	µs	
	• VLLS3 → RUN	—	—	96	µs	
	• VLPS → RUN	—	—	5.4	µs	
	• STOP → RUN	—	—	5.4	µs	

2.2.5 Power consumption operating behaviors

NOTE

The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean+3σ)

Table 6. Power consumption operating behaviors (All IDDs are Target values)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash, excludes IDDA					Core frequency of 25 MHz.
	• @ 1.8V	—	6.8	17.2	mA	
	• @ 3.0V	—	6.9	17.4	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash, excludes IDDA					Core frequency of 50 MHz.
	• @ 1.8V • @ 3.0V	—	9.9	19.7	mA	

Table continues on the next page...

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 10 MHz (crystal), f_{SYS} = 75 MHz, f_{BUS} = 25 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.nxp.com.
2. Perform a keyword search for “EMC design.”

2.2.8 Capacitance attributes

Table 9. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

2.3 Switching specifications

2.3.1 Typical device clock specifications

Table 10. Typical device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
High Speed RUN mode					
f_{SYS}	System and core clock	—	168	MHz	
f_{BUS}	Bus and Flash clock	—	24	MHz	
f_{FPCK}	Fast peripheral clock	—	84	MHz	
f_{NANO}	Nano-edge clock	—	168	MHz	
Normal run mode					
f_{SYS}	System and core clock	—	100	MHz	
f_{BUS}	Bus and Flash clock	—	25	MHz	

Table continues on the next page...

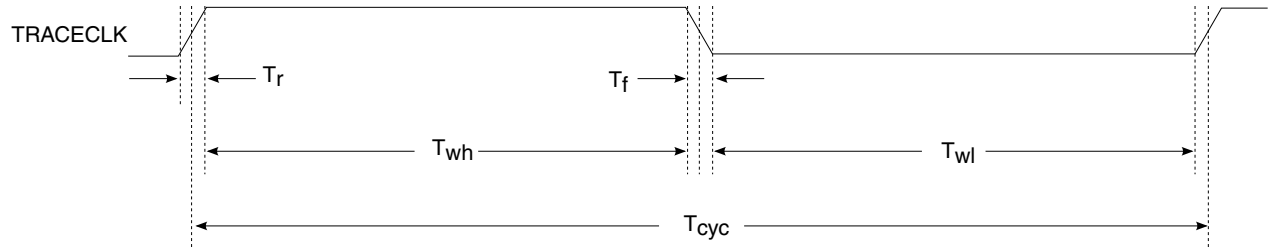

Figure 7. TRACE_CLKOUT specifications

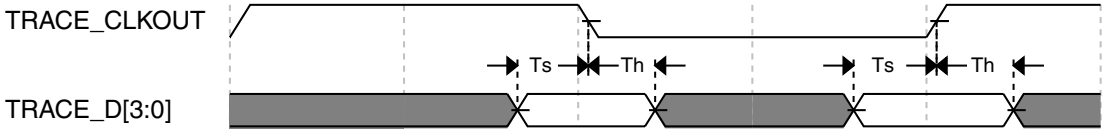

Figure 8. Trace data specifications

3.1.3 JTAG electricals

Table 16. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	25	
	• Serial Wire Debug	0	50	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	20	—	ns
	• Serial Wire Debug	10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	2.0	—	ns
J7	TCLK low to boundary scan output data valid	—	28	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns

Table continues on the next page...

Table 16. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J11	TCLK low to TDO data valid	—	19	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 17. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	20	
	• Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	2.0	—	ns
J7	TCLK low to boundary scan output data valid	—	30.6	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.0	—	ns
J11	TCLK low to TDO data valid	—	19.0	ns
J12	TCLK low to TDO high-Z	—	17.0	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

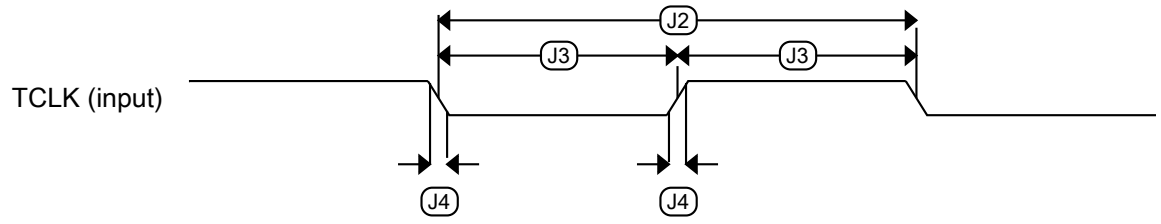

Figure 9. Test clock input timing

Table 19. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 8 MHz	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 12-bit cyclic Analog-to-Digital Converter (ADC) parameters

NOTE

The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean+3σ).

Table 25. 12-bit ADC electrical specifications

Characteristic	Symbol	Min	Typ	Max	Unit
Recommended Operating Conditions					
Supply Voltage[1]	V_{DDA}	2.7	3.3	3.6	V
V_{refh} Supply Voltage[2]	Vrefhx	2.7		V_{DDA}	V
ADC Conversion Clock[3]	f_{ADCCLK}	0.6		25	MHz
Conversion Range	R_{AD}	V_{REFL}		V_{REFH}	V
Input Voltage Range External Reference Internal Reference	V_{ADIN}	 V_{REFL} V_{SSA}		 V_{REFH} V_{DDA}	V
Timing and Power					
Conversion Time	t_{ADC}		6		ADC Clock Cycles
ADC Power-Up Time (from adc_pdn)	t_{ADPU}		13		ADC Clock Cycles
ADC RUN Current (per ADC block) • at 600 kHz ADC Clock, LP mode • ≤ 8.33 MHz ADC Clock, 00 mode • ≤ 12.5 MHz ADC Clock, 01 mode • ≤ 16.67 MHz ADC Clock, 10 mode • ≤ 20 MHz ADC Clock, 11 mode • ≤ 25 MHz ADC Clock	I_{ADRUN}		 1 5.7 10.5 17.7 22.6 27.5		mA
ADC Powerdown Current (adc_pdn enabled)	$I_{ADPWRDWN}$		0.02		µA
V_{REFH} Current	I_{VREFH}		0.001		µA
Accuracy (DC or Absolute)					
Integral non-Linearity[4]	INL		+/- 3	+/- 5	LSB[5]
Differential non-Linearity[4]	DNL		+/- 0.6	+/- 0.9	LSB[5]

Table continues on the next page...

Table 25. 12-bit ADC electrical specifications (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Monotonicity					
Offset[6] • 1x gain mode • 2x gain mode • 4x gain mode	V_{OFFSET}			 +/- 25 +/- 20 +50, -10	LSB[4]
Gain Error	E_{GAIN}		0.0002	—	%
AC Specifications[7]					
Signal to Noise Ratio	SNR		59		dB
Total Harmonic Distortion	THD		64		dB
Spurious Free Dynamic Range	SFDR		65		dB
Signal to Noise plus Distortion	SINAD		59		dB
Effective Number of Bits	ENOB		9.1		bits
ADC Inputs					
Input Leakage Current	I_{IN}		0	+/-2	µA
Input Injection Current [8]	I_{INJ}			+/-3	mA
Input Capacitance Sampling Capacitor	C_{ADI}		4.8		pF

1. If the ADC's reference is from V_{DDA}: When V_{DDA} is below 2.7 V, then the ADC functions, but the ADC specifications are not guaranteed.
2. When the input is at the V_{refl} level, then the resulting output will be all zeros (hex 000), plus any error contribution due to offset and gain error. When the input is at the V_{refh} level, then the output will be all ones (hex FFF), minus any error contribution due to offset and gain error.
3. ADC clock duty cycle min/max is 45/55% .
4. D_{NL} and I_{NL} conversion accuracy is not guaranteed from V_{REFL} to V_{REFL} + 0025 and V_{REFH} to V_{REFH}-0025.
5. LSB = Least Significant Bit = 0.806 mV at 3.3 V VDDA, x1 Gain Setting
6. Offset over the conversion range of 0025 to 4070, with internal/external reference.
7. Measured when converting a 1 kHz input Full Scale sine wave.
8. The current that can be *injected into* or *sourced from* an unselected ADC input, without affecting the performance of the ADC.

3.6.1.1 Equivalent circuit for ADC inputs

The following figure shows the ADC input circuit during sample and hold. S1 and S2 are always opened/closed at non-overlapping phases, and both S1 and S2 operate at the ADC clock frequency. The following equation gives equivalent input impedance when the input is selected.

$$\frac{1}{(\text{ADC ClockRate}) \times 1.4 \times 10^{-12}} + 100\,ohm + 125\,ohm$$

Table 28. 12-bit DAC operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	µs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) • High-speed mode • Low speed mode	—	1	5	µs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	µV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h • High power (SP_{HP}) • Low power (SP_{LP})	 1.2 0.05	 1.7 0.12	 — —	V/µs	
BW	3dB bandwidth • High power (SP_{HP}) • Low power (SP_{LP})	 550 40	 — —	 — —	kHz	

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

Table 35. Slave mode DSPI timing for fast pads (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		25	MHz
DS9	DSPI_SCK input cycle time	4 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) – 2	(t_{SCK}/2) + 2	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	17	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	11	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	11	ns

Table 36. Slave mode DSPI timing for open drain pads (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz
DS9	DSPI_SCK input cycle time	4 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) – 2	(t_{SCK}/2) + 2	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	28	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	22	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	22	ns

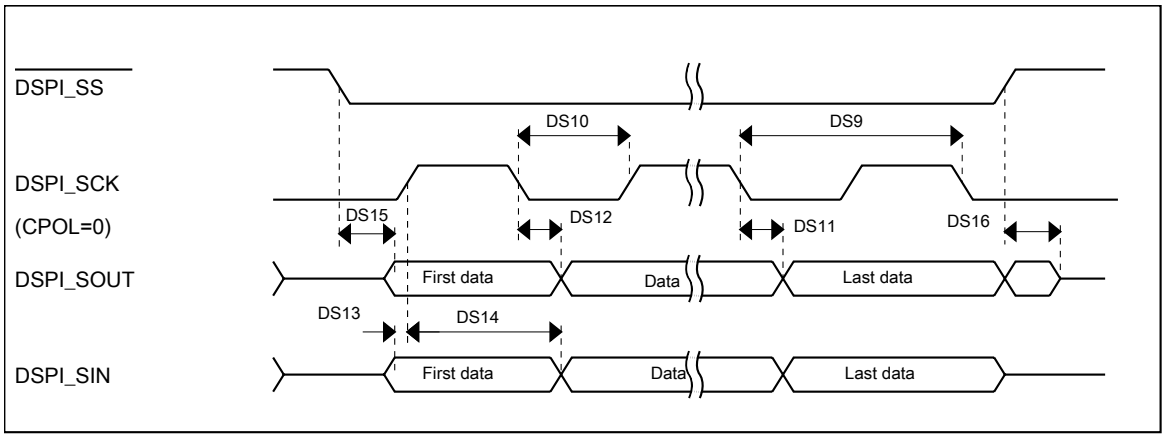

Figure 19. DSPI classic SPI timing — slave mode

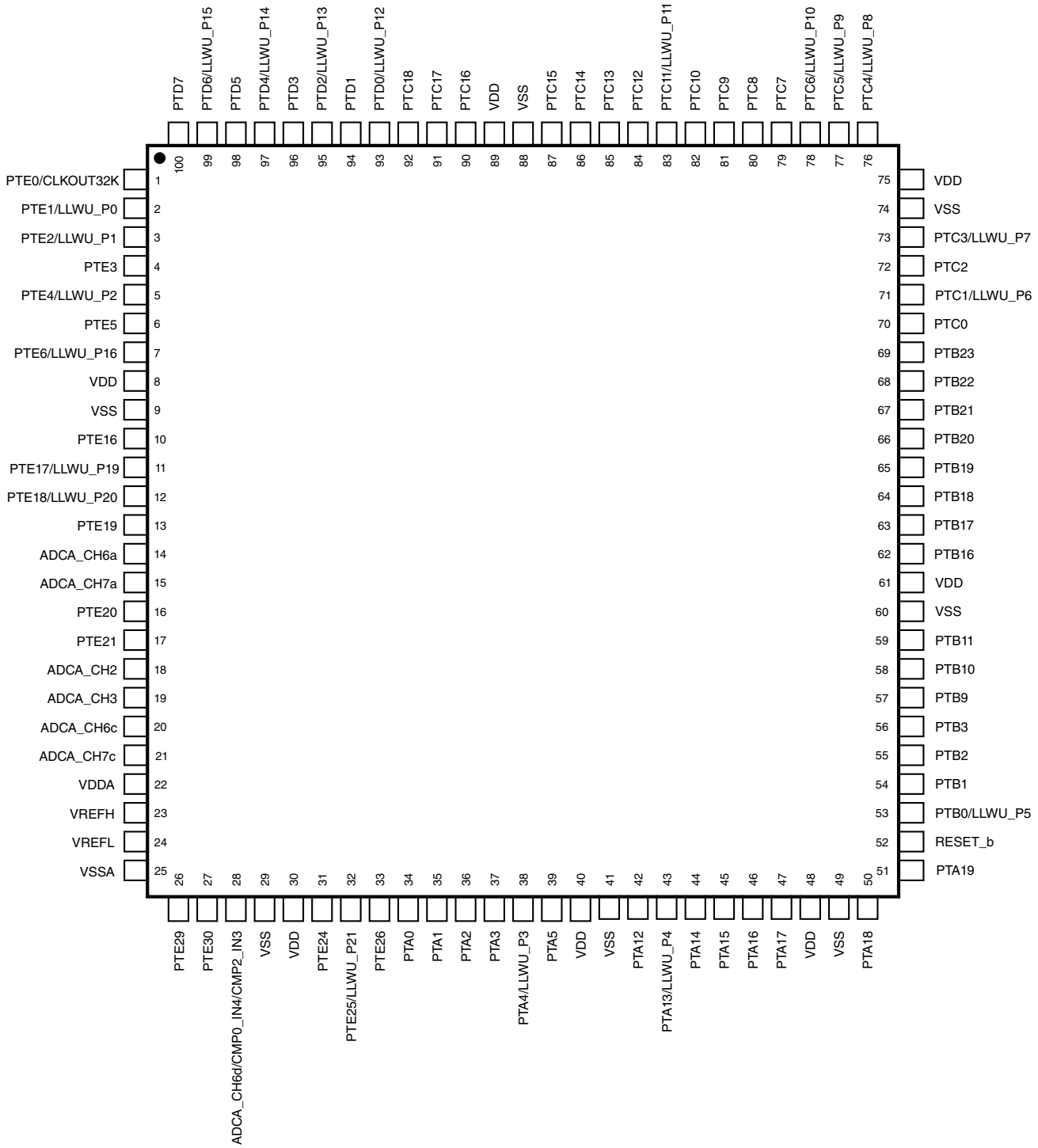

Figure 22. 100-pin LQFP

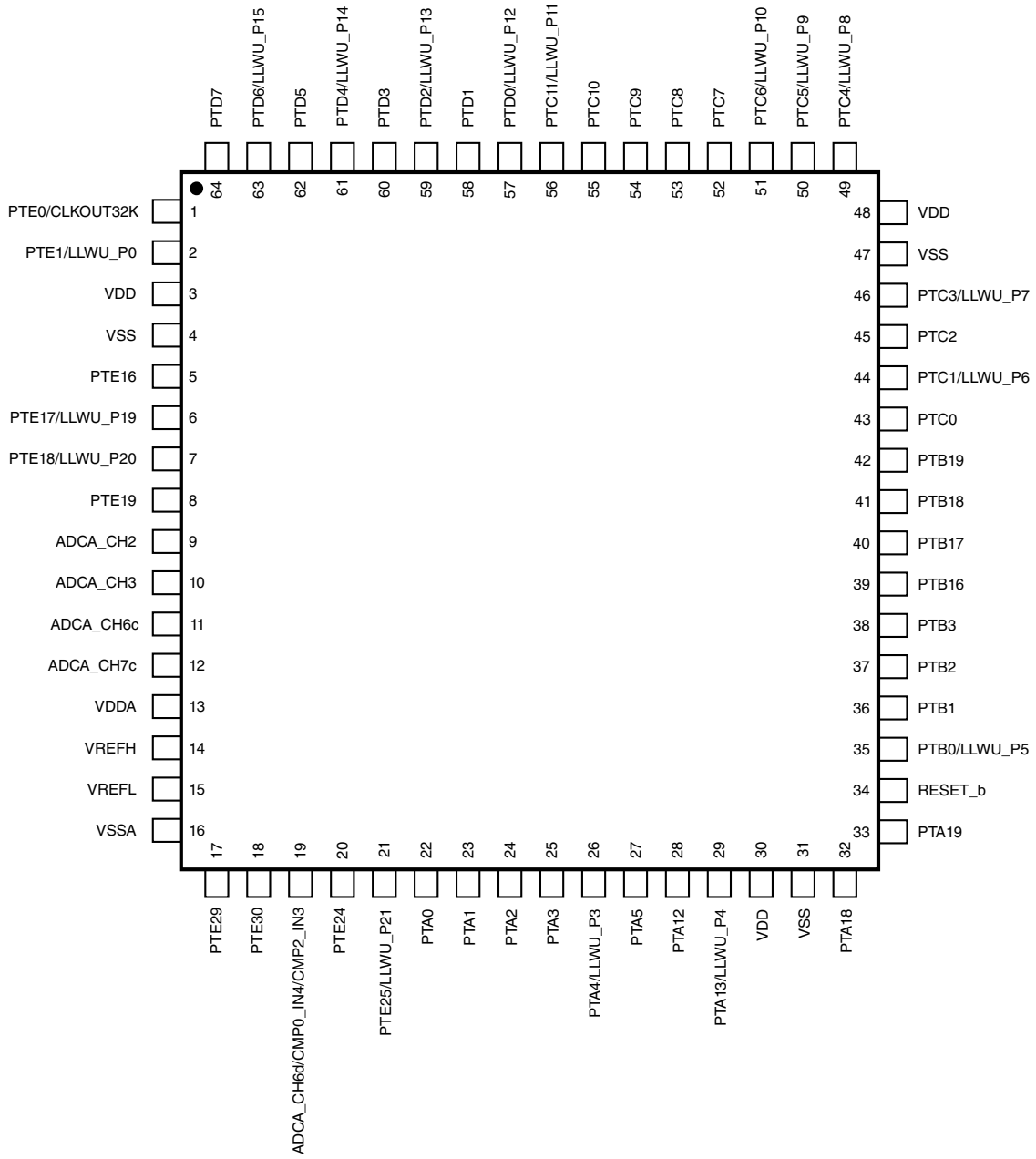

Figure 23. 64-pin LQFP

6.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.nxp.com and perform a part number search for the MKV4x device numbers.

7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KV## A FFF T PP CC S N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KV##	Kinetis family	• KV42 • KV44 • KV46
A	Key attribute	• F = Cortex-M4 w/ DSP and FPU
FFF	Program flash memory size	• 64 = 64 KB • 128 = 128 KB • 256 = 256 KB
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • LL = 100 LQFP (14 mm x 14 mm)
CC	Maximum CPU frequency (MHz)	• 16 = 168 MHz

Table continues on the next page...

Field	Description	Values
S	Software type	• P = KMS-PMSM and BLDC • (Blank) = Not software enabled
N	Packaging type	• R = Tape and reel • (Blank) = Trays

7.4 Example

This is an example part number:

MKV46F256VLL16

8 Terminology and guidelines

8.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

8.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

8.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

8.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

8.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

8.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

8.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

8.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

8.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

8.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

Table 43. Revision history (continued)

Rev. No.	Date	Substantial Changes
		• Obtaining package dimensions • Pinout • In table "Power consumption operating behaviors", removed the text "Maximum core fequency of 150 Mhz" from note for I_{DDA}. • In table "Typical device clock specifications", removed information about High Speed run mode.

2	8/2015	• Updated instances of operating frequency from 150 MHz to 168 Mhz
		• Changed document number from "KV4XP100M150" to "KV4XP100M168" due to the change in operating frequency
		• Part numbers ending with "15" changed to ending with "16"
		• Removed instances of MKV45, MKV43, and MKV40 part numbers
		• Updated MKV41 part numbers to MKV42
		• Added part numbers MKV44F256VLL16 and MKV44F256VLH16
		• Updated table "Orderable part numbers summary"
		• In table Recommended Operating Conditions :
		  • Updated minimum digital supply voltage to 1.71 V
		  • Added footnote numbers 2 and 3
		  • Removed rows for I_{OH}, I_{OL}, N_F, T_R, and t_{FLRET}
		• Updated table Voltage and current operating behaviors
		• Updated table Power mode transition operating behaviors
		• Updated table Power consumption operating behaviors
		• Updated table EMC radiated emissions operating behaviors
		• Updated table Typical device clock specifications
		• Updated table Thermal attributes
		• Updated the PLL section of table MCG specifications
		• Updated t_{ersall} value in table Flash timing specifications — commands
		• Added note to section 12-bit cyclic Analog-to-Digital Converter (ADC) parameters
		• Updated $I_{DDA\_DACL\ P}$ and $I_{DDA\_DACH\ P}$ values in table 12-bit DAC operating behaviors
		• Updated the pinouts
		• Added section Enhanced NanoEdge PWM characteristics

3	06/2016	• Changed occurences of Freescale to NXP • In the features list, added a section for "Kinetis Motor Suite" • Added section Kinetis Motor Suite (KMS) • In table 12-bit ADC electrical specifications, changed typical value of ENOB from 9.5 to 9.1